

Method for Coating and Bonding of Substrates

Specification

This invention relates to a method for coating of a first substrate with a first diffusion bond layer as claimed in Claim 1 and to a method for bonding as claimed in Claim 6.

The objective in permanent or irreversible bonding of substrates is to produce a connection as strong and especially as permanent as possible, therefore a high bond force, between the two contact surfaces of the substrates. For this purpose, in the prior art there are various approaches and production methods, especially the welding of the surfaces at higher temperatures.

All types of materials, predominantly however metals, semimetals, semiconductors, polymers and/or ceramics, are permanently bonded. One of the most important systems of permanent bonding is metal-metal systems. Mainly Cu-Cu systems have appeared increasingly in recent years. The development of 3D structures specifically requires mostly the joining of different functional layers. This joining is more and more often done by way of so-called TSVs (through silicon vias). The contact-making of these TSVs with one another very often takes place by copper contact sites. At the instant of bonding very often there are full-value, serviceable structures, for example microchips, on one or more surfaces of the substrates. Since different materials with different coefficients of thermal expansion are used in microchips, increasing the temperature during bonding is not desirable. This can lead to thermal expansions and thus to thermal stresses and/or stress induced voiding (SIV) which can destroy parts of the microchip or its vicinity.

The known production methods and the approaches which have been followed to date often

lead to results which cannot be reproduced or can be poorly reproduced and which can hardly be applied especially to altered conditions. In particular, production methods which are used at present often use high temperatures, especially $> 400^{\circ}\text{C}$, in order to ensure reproducible results.

Technical problems such as high energy consumption and a possible destruction of structures which are present on the substrates result from the high temperatures which have been necessary to date for a high bond force and the rapid and/or often completed temperature changes which arise due to loading and/or unloading, of in part far above 300°C .

Other demands consist in the following:

- back-end-of-line compatibility.

This is defined as the compatibility of the process during the processing. The bonding process must therefore be designed such that back-end-of-line structures, generally consisting of electrical conductors and low-k dielectrics which are already present on the structure wafers, are neither adversely affected nor damaged during the processing.

Compatibility criteria include mainly mechanical and thermal loadability, mainly by thermal stresses and stress induced voiding (SIV).

- front-end-of-line compatibility.

This is defined as the compatibility of the process during the production of the electrically active components. The bonding process must therefore be designed such that active components such as transistors which are already present on the structure wafers, are neither adversely affected nor damaged during the processing. Compatibility criteria include mainly the purity of certain chemical elements (mainly in CMOS structures), mechanical and thermal loadability, mainly by thermal stresses.

- low contamination.
- no application of force, or application of force as low as possible.
- temperature as low as possible, especially for materials with different coefficients of thermal expansion.

The reduction of the bond force leads to more careful treatment of the structure wafer and thus to a reduction of the failure probability by direct mechanical loading, especially when the insulating layers between the metallic conductors are made from so-called "low-k" materials.

Current bonding methods are designed primarily for high pressures and temperatures. Mainly avoiding a high temperature is of essential importance for the welding of future semiconductor applications, since different materials with different coefficients of thermal expansion generate thermal stresses which cannot be ignored during heating and cooling processes. Furthermore, the diffusion of doping elements as the temperature rises is increasingly becoming a problem. The doped elements should not leave the intended three-dimensional region after the doping process. Otherwise the physical properties of the circuits would fundamentally change. In the best case this leads to deterioration, in the worst and most probable case to unserviceability of the component. Mainly memories are very susceptible due to degradation of the dielectric and the associated shortened storage time during thermal processes. On the other hand, there are memories in which 3D technology is being increasingly used to raise the capacity and performance.

The object of this invention is therefore to devise a method for careful production of a permanent bond between two substrates with a bond force as high as possible at a temperature which is simultaneously as low as possible and/or at an average process time.

This object is achieved with the features of Claims 1 and 6. Advantageous developments of

the invention are given in the dependent claims. All combinations of at least two of the features given in the specification, the claims and/or the figures also fall within the framework of the invention. At the given value ranges values which lie within the indicated boundaries will also be considered disclosed as boundary values and will be claimed in any combination.

The basic idea of this invention is to apply or create at least on one of the substrates a diffusion bond layer of a material which has a microstructure with a grain as fine as possible, and thus a grain boundary surface as large as possible. As claimed in the invention mainly grain boundaries are preferred which run normally to the substrate surfaces which are to be bonded. This is achieved as claimed in the invention by controlled setting of the layer thickness of the diffusion bond layer which constitutes a limiting criterion for the grain size. The two substrates can, but need not necessarily, prebond with one another. Simple contact-making without formation of a prebond is also possible. As claimed in the invention the term "reaction" should be understood as solid diffusion. Before and/or after formation/application of the diffusion bond layer(s) on the first and/or second substrate, cleaning of the substrate or of the substrates generally takes place, especially by a rinsing step. This cleaning should generally ensure that there are no particles on the surfaces which would result in unbonded sites. Ideally all steps of deposition and/or bonding as claimed in the invention take place in a closed system which is preferably flooded with inert gas, more preferably evacuated so that a cleaning step after coating can be omitted.

The heart of this invention is to form the diffusion bond layer at least on the contact surface between the first and second substrate with an average grain diameter H parallel to the contact surface or substrate surface smaller than $1\text{ }\mu\text{m}$.

The diffusion bond layer which is formed in this way and which has a small average grain

diameter creates the technical possibility of causing faster diffusion directly on the contact surfaces between the substrates and thus enabling the permanent bond primarily at low temperatures and furthermore strengthening it, and increasing the bond speed.

Hereinafter deformation is defined as a change of the surface and/or of the bulk as a result of diffusion.

All elements of the periodic table, mainly the metals, semimetals, lanthanoids and actinoids are possible as materials as claimed in the invention for the diffusion bond layer.

Especially preferably the invention however is used for Cu-Cu bonds.

The following mixed forms of semiconductors are conceivable as substrates:

- III-V: GaP, GaAs, InP, InSb, InAs, GaSb, GaN, AlN, InN, $\text{Al}_x\text{Ga}_{1-x}\text{As}$, $\text{In}_x\text{Ga}_{1-x}\text{N}$
- IV-IV: SiC, SiGe,
- III-VI: InAlP,
- nonlinear optics: LiNbO_3 , LiTaO_3 , KDP (KH_2PO_4)
- solar cells: CdS, CdSe, CdTe, CuInSe_2 , CuInGaSe_2 , CuInS_2 , CuInGaS_2
- conductive oxides: $\text{In}_{2-x}\text{Sn}_x\text{O}_{3-y}$

It is especially advantageous as claimed in the invention if contact-making of the substrates after application of the diffusion bond layer takes place as near as possible in time, especially within 2 hours, preferably within 30 minutes, even more preferably within 10 minutes, ideally within 5 minutes. This measure minimizes possible unwanted reactions such as oxidation of the metal diffusion bond layer or of the surfaces of the substrates.

Oxide removal before the actual bonding process is also possible. The oxide can be removed for example by wet-chemical means or with corresponding reducing gases. Any known

chemical and/or physical methods for oxide reduction can be used.

As claimed in the invention there can be means for inhibiting these reactions of the metal diffusion bond layer and/or of the surfaces of the substrates before the contact surfaces make contact, especially by passivation of the surfaces of the substrates, preferably by exposure to N₂, forming gas or an inert atmosphere or under a vacuum or by amorphization. In this connection treatment with plasma which contains forming gas, especially consists largely of forming gas, has proven especially suitable. Here forming gas is defined as gases which contain at least 2%, better 4%, ideally 10% or 15% hydrogen. The remaining portion of the mixture consists of an inert gas such as for example nitrogen or argon. Systems with an inert atmosphere or vacuum atmosphere can preferably be implemented as systems in which the transfer of the substrates from one process chamber to the next process chamber takes place by means of a substrate handling system which can carry out the transfer of the substrates completely in a controlled, adjustable atmosphere, especially a vacuum atmosphere. These systems are known to one skilled in the art.

The diffusion bond layer is applied by one or more of the following methods:

- CVD especially PECVD, LPCVD, MOCVD or ALD
- PVD especially sputtering or vapor deposition
- epitaxy especially MBE, ALE
- electrochemical deposition processes
- currentless deposition processes

The invention thus solves the problem of better welding of the surfaces of two coated substrates which have been brought into contact with one another by using the microstructure properties of the uppermost layer, the diffusion bond layer. The invention thus relates to a method

and a process for adjusting the microstructure of the uppermost deposited layer by the controlled deposition of thin layers by means of chemical and/or physical processes such that its grain interface is as large as possible. Preferably the grain boundaries run normally to the substrate surface.

The grain size which is small as claimed in the invention yields an extremely increased grain boundary surface and thus accordingly larger diffusion paths; this promotes the welding of the two material layers during bonding. The idea as claimed in the invention therefore consists in increasing the flow of those atoms which diffuse along the grain boundaries by increasing the grain boundary surface.

According to another advantageous embodiment of the invention, it is provided that the formation of the permanent bond takes place at a temperature between room temperature and 400°C, especially between room temperature and 300°C, preferably between room temperature and 200°C, even more preferably between room temperature and 100°C, especially during a maximum 12 days, preferably a maximum 1 day, even more preferably a maximum 1 hour, best a maximum 15 minutes.

Here it is especially advantageous if the irreversible bond has a bond strength of greater than 1.5 J/m², especially greater than 2 J/m², preferably greater than 2.5 J/m². The bond strength can be determined for example with the so-called Maszara test.

The bond strength can be increased especially advantageously in that the two substrates have a diffusion bond layer with a grain size which is very small as claimed in the invention, and thus a very large grain boundary surface. This enables increased diffusion flow in both directions which accordingly supports the bond process.

To the extent prior to application/formation of the function layer plasma activation of the surfaces of the substrates takes place especially with an activation frequency between 10 and 600 kHz and/or a power density between 0.075 and 0.2 watt/cm² and/or with application of a pressure between 0.1 and 0.6 mbar, additional effects such a smoothing of the contact surface are caused. Here application of pressure is defined as the pressure of the working atmosphere during plasma activation.

To the extent the substrates are pressed together at a pressure between 0.1 MPa and 10 MPa, optimum results can be achieved. Preferably the pressure is between 0.1 and 10 MPa, still more preferably between 0.1 and 1 MPa, most preferably between 0.1 and 0.3 MPa. The pressure must be chosen to be greater, the larger the irregularities and the thinner the layers.

Advantageously according to one embodiment of the invention it is provided that the formation/application of the diffusion bond layer is carried out in a vacuum. Thus the contamination of the diffusion bond layer with unwanted materials or compounds can be avoided.

It is especially effective for the sequence of the method if the diffusion bond layer is made preferably in an average thickness R between 0.1 nm and 2500 nm, more preferably between 0.1 nm and 150 nm, even more preferably between 0.1 nm and 10 nm, most preferably between 0.1 nm and 5 nm.

Other advantages, features and details of the invention will become apparent from the following description of preferred exemplary embodiments and using the drawings.

Figure 1 shows a cross section of two substrates which have been coated as claimed in the invention with a layer system,

Figure 2 shows a diffusion bond layer as claimed in the invention,

Figure 3 shows an intermediate layer as claimed in the invention,

Figure 4 shows a diffusion bond layer applied to a substrate,

Figure 5 shows a layer system applied to a substrate with one intermediate layer and one diffusion bond layer and

Figure 6 shows a layer system applied to a substrate with two intermediate layers and one diffusion bond layer.

The same or equivalent features are identified with the same reference numbers in the figures. The drawings are not to scale. Mainly the intermediate layers and diffusion bond layer are shown several times larger to be able to better represent the microstructure.

The invention relates to a method for bonding of two coated substrates 1, 3 to one another via two layer systems 2, 4. The layer systems 2, 4 can be composed of any number of layers 5, 5', 5'' of different type (intermediate layers 5', 5'' and diffusion bond layer 5) with different physical and/or chemical properties and microstructures. As claimed in the invention the layer which is uppermost at the time (contact surface between the layer systems 2, 4) is a diffusion bond layer 5, therefore a layer whose grain size is limited as claimed in the invention.

The diffusion bond layer 5 which is applied to the first surface of the first substrate 1 is called the first diffusion bond layer and the one applied to a second surface 3o of the second substrate 3 is called the second diffusion bond layer.

The average grain diameter H of the surface 1o, 3o, of the substrates 1, 3, which diameter is projected parallel to the surface (plan view), is preferably less than 1 μm , more preferably less than 100 nm, still more preferably less than 10 nm, even more preferably less than 5 nm, most preferably less than 1 nm.

The average grain diameter V which is measured orthogonally to the average grain diameter H or to the substrate surface is preferably less than $1\text{ }\mu\text{m}$, more preferably less than 100 nm , still more preferably less than 10 nm , even more preferably less than 5 nm , most preferably less than 1 nm .

The projected grain diameters H and V are not necessarily the same. But for very thin layer thickness t , H and V are presumably of the same order of magnitude. In this case V or t limits the grain diameter. This is due to the surface energy which prevents enlargement of the grain. In the embodiment as shown in Figure 2 the vertical grain diameter V is stipulated as limiting by a layer thickness t of the layer system 2 consisting of only a single diffusion bond layer 5 here. Then a layer thickness t of the layer system 2 is equal to the grain diameter V .

In the embodiment shown in Figure 4 the diffusion bond layer 5 with a grain interface as large as possible is deposited directly on the first substrate 1.

In another embodiment as claimed in the invention as shown in Figure 5, the diffusion bond layer 5 with a grain interface as large as possible (therefore with many grain boundaries) is deposited on any other intermediate layer 5'. The intermediate layer 5' can be the same material with optionally different distribution of the grain size as in the diffusion bond layer 5. The microstructure on the contact surface (surface of the diffusion bond layer 5) was influenced especially exclusively by the deposition process. In particular the intermediate layer 5' was produced by an electrochemical deposition process (ECD) or PVD process, conversely the diffusion bond layer 5 is produced by PVD and/or CVD processes.

The intermediate layer 5' as shown in Figure 3 has a larger average grain diameter H' parallel to the surface 1o or 3o and a larger average grain diameter V' transversely to the surface 1o

or 3o. Here it is also advantageous if the layer thickness t' of the intermediate layer 5' is larger, especially twice as large, preferably 3 times, more preferably 5 times, still more preferably 10 times, most preferably 100 times, most preferably of all 1000 times as large as the average grain diameter V .

In another embodiment as claimed in the invention as shown in Figure 6, another intermediate layer 5" is deposited between the diffusion bond layer 5 and the intermediate layer 5'. The intermediate layer 5" has the task as claimed in the invention of preventing a possible interdiffusion between the diffusion bond layer 5 and the intermediate layer 5' so that the microstructure of the diffusion bond layer 5 is preserved up to the actual bond process.

More efficient diffusion of the atoms from the layer system 2 into the layer system 4 and vice versa takes place by a subsequent bond process of the two substrates 1, 3 via their layer systems 2,4 as claimed in the invention by the large grain interface (and thus a large number of grain boundaries) of at least one diffusion bond layer.

As claimed in the invention the diffusion bond layer 5 is the layer which forms the contact surface. The reason is that the diffusion bond layer 5 has a very large number of grain boundaries 7. The average diffusion flow takes place therefore preferably in the vertical direction (transversely to the surface 1o, 3o) along these grain boundaries 7.

The intrinsic diffusion of a species along one free surface is greater than along the grain boundaries, but along the grain boundaries greater than within the bulk. Preferably therefore the "interdiffusion" of the atoms of the two layer systems 2 and 4 into one another over the grain boundaries will take place by the large number of grain boundaries as claimed in the invention.

The bonding of the two layer systems 2 and 4 takes place preferably at temperatures as low

as possible. For metals the bonding takes place preferably at a homologous temperature of less than 1.0 but above room temperature and below a temperature of 300°C.

Layer systems as claimed in the invention would be especially the following:

- Si substrate / thin diffusion barrier / thick (ECD) Cu layer / thin diffusion barrier (for example Ti, Ta,...) / thin (PVD) Cu layer
- Si substrate / thin diffusion barrier / thick (ECD) Cu layer / thin (PVD) Cu layer
- Si substrate / thin diffusion barrier / thin (PVD) Cu layer
- Si substrate / thin diffusion barrier / Cu layer / thin Si layer
- Si substrate / thin diffusion barrier / Cu layer / thin layer of a transition metal (Ti, Ta, W,...)
- Si substrate / thin diffusion barrier / Cu layer / thin layer of a precious metal (Au, Pd,...)
- any combination of the aforementioned layer systems

The bond process can take place as claimed in the invention by the bonding of any of the aforementioned layer systems to any other of the aforementioned layer systems. Analogous considerations apply to any other layer system which is not mentioned explicitly in the text, but which is based on the same inventive idea.

The method which is preferred as claimed in the invention for producing the intermediate layers 5', 5'' with comparatively large grain sizes (compared to the diffusion bond layer 5) is electrochemical deposition (ECD).

The method which is preferred as claimed in the invention for producing the diffusion bond layer 5 with comparatively small grain sizes are all PVD and/or CVD method.

Reference number list

1	first substrate
1o	surface
2	layer system
3	second substrate
3o	surface
4	layer system
4o, 4o'	surface
5	diffusion bond layer
5', 5"	intermediate layers
6	grain
7	grain boundary
t, t'	layer thickness
H, H'	(average) grain diameter
V, V'	(average) grain diameter

Claims

1. A method for coating of a first substrate (1) with a first diffusion bond layer (5) by deposition of a first material which forms the first diffusion bond layer (5) on a first surface (1o) of the first substrate (1) such that the first diffusion bond layer (5) forms a grain surface with an average grain diameter H parallel to the first surface (1o) smaller than $1\text{ }\mu\text{m}$.

2. The method as claimed in Claim 1, wherein the first diffusion bond layer (5) on the grain surface forms an average grain diameter V transversely to the first surface (1o) less than $1\text{ }\mu\text{m}$, especially less than 100 nm , preferably less than 10 nm , even more preferably less than 1 nm

3. The method as claimed in one of the preceding claims, wherein the first diffusion bond layer (5) is applied with an average thickness t transversely to the first surface (1o) less than $1\text{ }\mu\text{m}$, especially less than 100 nm , preferably less than 10 nm , even more preferably less than 1 nm .

4. The method as claimed in one of the preceding claims, wherein between the first diffusion bond layer (5) and the first substrate (1) at least one further intermediate layer (5', 5'') which has been produced especially by an electrochemical deposition process is formed.

5. The method as claimed in one of the preceding claims, wherein the first diffusion bond layer (5) is produced by physical gaseous phase deposition and/or chemical gaseous phase deposition.

6. A method for bonding of a first substrate (1) coated as claimed in one of Claims 1 to 5 with a second substrate (3) which has a second diffusion bond layer or a substrate with a "standard layer" with the following steps, especially the following sequence:

- contact-making of the first diffusion bond layer (5) of the first substrate (1) with the second

- diffusion bond layer of the second substrate (3) or a substrate with a "standard layer",
- pressing the substrates (1, 3) together for forming a permanent metal diffusion bond between the first and second substrate (1, 3).

7. The method as claimed in Claim 6, wherein the permanent bond has a bond strength of greater than 1.5 J/m^2 , especially greater than 2 J/m^2 , preferably greater than 2.5 J/m^2 .

8. The method as claimed in Claim 6 or 7, wherein the pressing together takes place at a pressure between 0.1 and 10 MPa.

9. The method as claimed in one of Claims 6 to 8, wherein the first and/or the second diffusion bond layer (5) are made such that the diffusion bond layer takes place as solid diffusion, especially at least largely as grain boundary diffusion.

10. The method as claimed in one of Claims 6 to 9, wherein the formation of the permanent bond takes place at a temperature between room temperature and 500°C , especially between room temperature and 200°C , preferably between room temperature and 150°C , even more preferably between room temperature and 100°C , most preferably between room temperature and 50°C , especially during a maximum 12 days, preferably a maximum 1 day, even more preferably a maximum 1 hour, best a maximum 15 minutes.